

60V N-Channel Enhancement Mode MOSFET

Voltage 60 V Current 5 A

Features

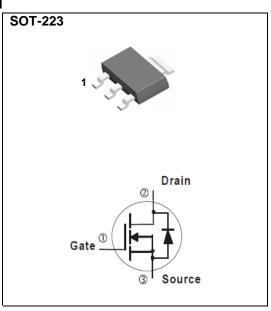
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@5A<75m\Omega$
- R_{DS(ON)}, V_{GS}@4.5V, I_D@3A<90mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: SOT-223 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.043 ounces, 0.123grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V _{GS}	<u>+</u> 20		
Continuous Drain Current (Note 4)	T _A =25°C	I _D	5		
	T _A =70°C		4	А	
Pulsed Drain Current (Note 1)		I _{DM}	20		
Power Dissipation	T _A =25°C	P _D	3.1	W	
	T _A =70°C		2		
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Typical Thermal Resistance - Junction to Ambient (Note 4,5)		R _{θJA}	40.3	°C/W	

• Limited only By Maximum Junction Temperature



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	BV _{DSS} V _{GS} =0V, I _D =250uA		-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =250uA	1	1.8	2.5	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =5A	-	53	75	mΩ	
		V _{GS} =4.5V, I _D =3A	-	61	90		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 6)							
Total Gate Charge	Qg	V _{DS} =48V, I _D =3A, V _{GS} =10V (Note 2,3)	-	9.3	-	nC	
Gate-Source Charge	Qgs		-	2.2	-		
Gate-Drain Charge	Qgd	VGS=10V (10.62,0)	-	1.9	-		
Input Capacitance	Ciss	151/1/ 01/	-	509	-	pF	
Output Capacitance	Coss	V _{DS} =15V, V _{GS} =0V, f=1MHZ	-	47	-		
Reverse Transfer Capacitance	Crss	I=IIVIMZ	-	23	-		
Turn-On Delay Time	td(on)	\/ 00\/ I 0A	-	3.2	-		
Turn-On Rise Time	tr	V _{DD} =30V, I _D =3A, V _{GS} =10V,	-	9.7	-	ns	
Turn-Off Delay Time	td(off)		-	18.5	-		
Turn-Off Fall Time	tf	R _G =3.3Ω (Note 2,3)	-	6.4	-		
Drain-Source Diode							
Maximum Continuous Drain-Source			-	-	5	А	
Diode Forward Current	I _S						
Diode Forward Voltage	V_{SD}	I _S =1A, V _{GS} =0V	-	0.75	1	V	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

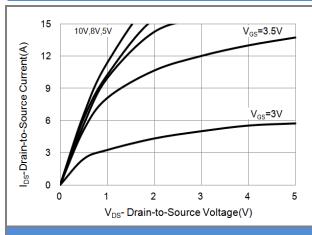


Fig.1 Output Characteristics

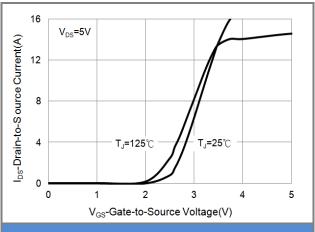


Fig.2 Transfer Characteristics

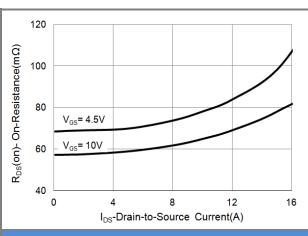


Fig.3 On-Resistance vs. Drain Current

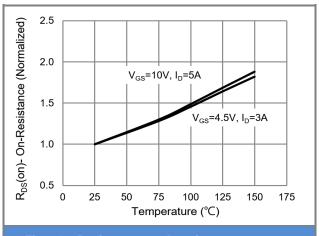


Fig.4 On-Resistance vs. Junction temperature

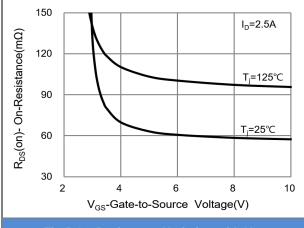


Fig.5 On-Resistance Variation with V_{GS}

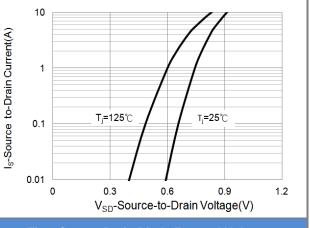


Fig.6 Source-Drain Diode Forward Voltage



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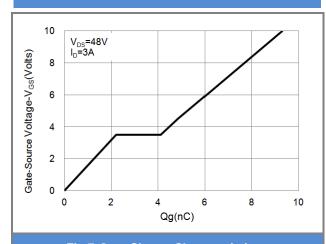


Fig.7 Gate-Charge Characteristics

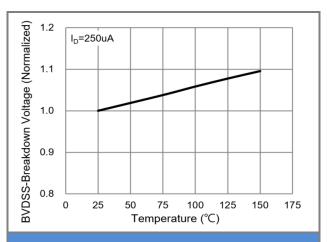


Fig.8 Breakdown Voltage Variation vs. Temperature

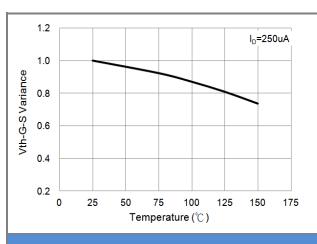


Fig.9 Threshold Voltage Variation with Temperature

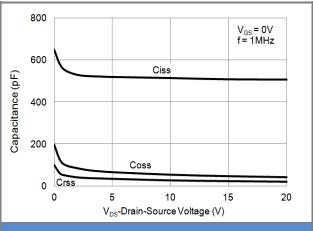


Fig.10 Capacitance vs. Drain-Source Voltage

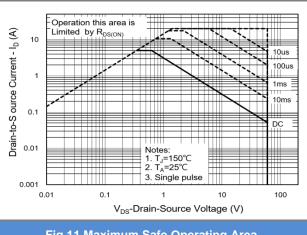


Fig.11 Maximum Safe Operating Area

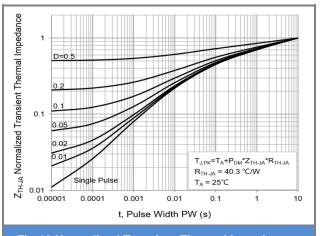


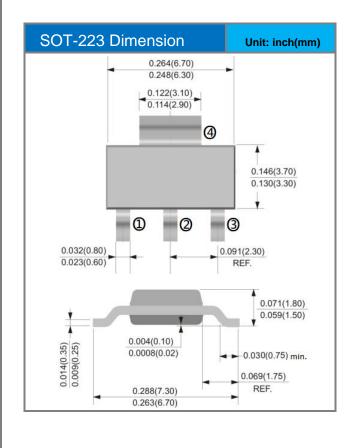
Fig.12 Normalized Transient Thermal Impedance

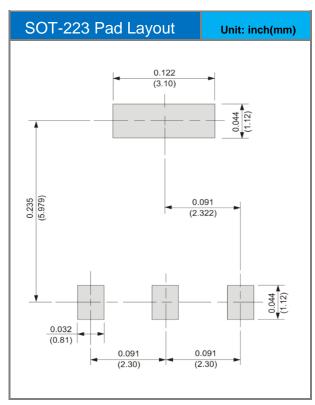


Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJW5N06A	SOT-223	2,500pcs / 13" reel	W5N06A

Packaging Information & Mounting Pad Layout







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